

Enhanced ferroelectricity in ultrathin films grown directly

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Citation Report

#	ARTICLE	IF	CITATIONS
1	The future of ferroelectric field-effect transistor technology. <i>Nature Electronics</i> , 2020, 3, 588-597.	13.1	398
2	Solution-Based Synthesis of Layered Two-Dimensional Oxides as Broadband Emitters. <i>ACS Nano</i> , 2020, 14, 15544-15551.	7.3	5
3	Recent advances, perspectives, and challenges in ferroelectric synapses*. <i>Chinese Physics B</i> , 2020, 29, 097701.	0.7	19
4	Hafnia-Based Double-Layer Ferroelectric Tunnel Junctions as Artificial Synapses for Neuromorphic Computing. <i>ACS Applied Electronic Materials</i> , 2020, 2, 4023-4033.	2.0	83
5	Reliability aspects of ferroelectric TiN/Hf _{0.5} Zr _{0.5} O ₂ /Ge capacitors grown by plasma assisted atomic oxygen deposition. <i>Applied Physics Letters</i> , 2020, 117, 212905.	1.5	22
6	Ferroelectric tunnel junctions with high tunnelling electroresistance. <i>Nature Electronics</i> , 2020, 3, 440-441.	13.1	18
7	Compositional dependence of linear and nonlinear optical response in crystalline hafnium zirconium oxide thin films. <i>Journal of Applied Physics</i> , 2020, 128, .	1.1	19
8	Flexible Quasi-van der Waals Ferroelectric Hafnium-Based Oxide for Integrated High-Performance Nonvolatile Memory. <i>Advanced Science</i> , 2020, 7, 2001266.	5.6	32
9	FerroElectronics for Edge Intelligence. <i>IEEE Micro</i> , 2020, 40, 33-48.	1.8	46
10	Single-Crystal-like Textured Growth of CoFe ₂ O ₄ Thin Film on an Amorphous Substrate: A Self-Bilayer Approach. <i>ACS Applied Electronic Materials</i> , 2020, 2, 3650-3657.	2.0	49
11	Tunable Microwave Filters Using HfO ₂ -Based Ferroelectrics. <i>Nanomaterials</i> , 2020, 10, 2057.	1.9	11
12	Ferroelectric Switching in Trilayer Al ₂ O ₃ /HfZrO _x /Al ₂ O ₃ Structure. <i>Micromachines</i> , 2020, 11, 910.	1.4	7
13	Revealing Antiferroelectric Switching and Ferroelectric Wakeup in Hafnia by Advanced Piezoresponse Force Microscopy. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 41659-41665.	4.0	18
14	Epitaxial Ferroelectric La-Doped Hf _{0.5} Zr _{0.5} O ₂ Thin Films. <i>ACS Applied Electronic Materials</i> , 2020, 2, 3221-3232.	2.0	48
15	Emergent Ferroelectricity in Otherwise Nonferroelectric Oxides by Oxygen Vacancy Design at Heterointerfaces. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 45602-45610.	4.0	15
16	Exploring Ferroelectric Switching in In ₂ Se ₃ for Neuromorphic Computing. <i>Advanced Functional Materials</i> , 2020, 30, 2004609.	7.8	119
17	Beyond Expectation: Advanced Materials Design, Synthesis, and Processing to Enable Novel Ferroelectric Properties and Applications. <i>MRS Advances</i> , 2020, 5, 3453-3472.	0.5	1
18	Impact of Interface Traps on Negative Capacitance Transistor: Device and Circuit Reliability. <i>IEEE Journal of the Electron Devices Society</i> , 2020, 8, 1193-1201.	1.2	33

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